

In the Claims

Claims 20-24, 26, 27, 35, and 45-49 are pending in the application with claims 1-7, 36-38, and 53-56 cancelled herein.

Claims 1-19 (cancelled).

20. (previously presented) A dielectric material forming method comprising:

chemisorbing alternated monolayers of a first dielectric material and a second dielectric material over a substrate; and

providing fewer monolayers of the second material compared to the first material with 2-20% of the monolayers being monolayers of the second material, the first material comprising tantalum and oxygen and the second material comprising oxygen, titanium, and zirconium.

21. (previously presented) The method of claim 20 wherein from about 5% to about 15% of the monolayers are second material monolayers.

22. (original) The method of claim 20 further comprising approximately evenly interspersing the second material monolayers among the first material monolayers.

23. (original) The method of claim 20 further comprising chemisorbing a majority of the second material monolayers on an underlying second material monolayer.

24. (original) The method of claim 20 wherein the first material comprises tantalum pentoxide.

Claim 25 (cancelled).

26. (original) The method of claim 20 wherein the chemisorbing of the monolayers comprises atomic layer depositing.

27. (original) The method of claim 20 further comprising annealing the monolayers.

Claims 28-34 (cancelled).

35. (previously presented) A dielectric material forming method comprising:

atomic layer depositing a plurality of monolayers, each of the plurality of monolayers comprising both an oxide of zirconium and tantalum oxide; and forming a dielectric material comprising the zirconium oxide and the tantalum oxide, the dielectric material exhibiting a dielectric constant greater than that of tantalum oxide and zirconium oxide.

Claims 36-44 (cancelled).

45. (previously presented) An enhanced dielectric material comprising alternated chemisorbed monolayers of a first dielectric material and a second dielectric material over a substrate, the enhanced dielectric material comprising fewer monolayers of the second material compared to the first material with 2-20% of the monolayers being monolayers of the second material, the first material comprising tantalum and oxygen, and the second material comprising oxygen, titanium, and zirconium.

46. (previously presented) The dielectric of claim 45 wherein from about 5% to about 15% of the monolayers are second material monolayers.

47. (original) The dielectric of claim 45 wherein the second material monolayers are approximately evenly interspersed among the first material monolayers.

48. (original) The dielectric of claim 45 wherein a majority of the second material monolayers contact an underlying second material monolayer.

49. (original) The dielectric of claim 45 wherein the first material comprises tantalum pentoxide.

Claims 50-56 (cancelled).